

L Number	Hits	Search Text	DB	Time stamp
13	21	(US-6327187-\$ or US-5739569-\$ or US-6465306-\$ or US-6445030-\$ or US-6436768-\$ or US-4353083-\$ or US-6418040-\$ or US-6005809-\$ or US-4635229-\$ or US-6448137-\$ or US-6426897-\$ or US-5493141-\$).did. or (US-20020151123-\$ or US-20020060929-\$ or US-20020032891-\$ or US-20030096476-\$ or US-20030075773-\$ or US-20030067807-\$ or US-20030128591-\$ or US-20030067809-\$).did. or (JP-2001229683-\$).did.	USPAT; US-PGPUB; JPO	2003/08/12 20:00
16	9	((US-6327187-\$ or US-5739569-\$ or US-6465306-\$ or US-6445030-\$ or US-6436768-\$ or US-4353083-\$ or US-6418040-\$ or US-6005809-\$ or US-4635229-\$ or US-6448137-\$ or US-6426897-\$ or US-5493141-\$).did. or (US-20020151123-\$ or US-20020060929-\$ or US-20020032891-\$ or US-20030096476-\$ or US-20030075773-\$ or US-20030067807-\$ or US-20030128591-\$ or US-20030067809-\$).did. or (JP-2001229683-\$).did.) and sonos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 20:00
-	116	(nitride adj3 tunnel\$3) with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 19:42
-	25	((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:40
-	3	((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)) and (charge adj3 trap\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:44
-	854	(first adj3 voltage) and (substrate adj3 ground)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:45
-	161	((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/22 16:46
-	5	((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)) and ((hot adj3 electron) with channel) and (inject\$3 same (charge with trap\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:19
-	1756	SONOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:20
-	7	SONOS and (nitride adj2 tunnel\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:21
-	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:26

-	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive ground gate substrate drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:27
-	0	(drain with (positive adj2 (voltage bias))) and (gate with (positive adj2 (voltage bias))) and (substrate with ground\$3) and (source with gound\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:45
-	58434	eras\$3 and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:27
-	1	(eras\$3 and memory) and (nitride adj2 tunneling adj2 layer) and (charge near2 trap\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:28
-	1	(eras\$3 and memory) and (nitride adj2 tunneling adj2 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:29
-	101	(eras\$3 and memory) and ((nitride adj2 tunneling adj2 layer) SONOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:29
-	35	(eras\$3 and memory) and ((nitride adj2 tunneling adj2 layer) SONOS) and (charge near2 trap\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:31
-	33	((eras\$3 and memory) and ((nitride adj2 tunneling adj2 layer) SONOS) and (charge near2 trap\$4)) and drain and source and substrate and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:32
-	0	(drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (substrate with ground\$3) and (source with gound\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:48
-	2315	(drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:49
-	0	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate near3 ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:50
-	1044	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:50
-	0	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (substrate near3 ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:50
-	469	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3) and (substrate same ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:51

-	354	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:52
-	9	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3)) and SONOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:56
-	9	((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3)) and SONOS) and eras\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 17:59
-	1190	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 12:55
-	369	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and ((positive adj3 (bias potential voltage)) near3 drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 12:56
-	616	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and ((positive adj3 (bias potential voltage)) near3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 12:59
-	681	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and (ground near3 source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 12:56
-	206	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and ((positive adj3 (bias potential voltage)) near3 drain)) and ((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and ((positive adj3 (bias potential voltage)) near3 gate)) and ((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and (ground near3 source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 12:57
-	69	((positive adj3 (bias potential voltage)) near3 drain) same (ground near3 source) same ((positive adj3 (bias potential voltage)) near3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 13:04
-	26	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and ((positive adj3 (bias potential voltage)) near3 drain) same (ground near3 source) same ((positive adj3 (bias potential voltage)) near3 gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 13:00
-	138	((positive high) adj3 (bias potential voltage)) near3 drain) same (ground near3 source) same ((positive high) adj3 (bias potential voltage)) near3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 13:05

-	43	((non-volatile nonvolatile flash) and (eras\$3 same (drain and source and gate and (positive near3 (bias potential voltage)) and ground))) and (((positive high) adj3 (bias potential voltage)) near3 drain) same (ground near3 source) same (((positive high) adj3 (bias potential voltage)) near3 gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 13:05
-	120	(nitride adj3 tunnel\$3) near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 20:39
-	2	(hot adj2 electron) with ((nitride adj3 tunnel\$3) near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 20:40
-	13	(US-6465306-\$ or US-6445030-\$ or US-6436768-\$ or US-6418040-\$ or US-6327187-\$ or US-6005809-\$ or US-4353083-\$ or US-4635229-\$ or US-5739569-\$ or US-6448137-\$).did. or (US-20020151123-\$ or US-20020032891-\$ or US-20020060929-\$).did.	USPAT; US-PGPUB	2003/07/15 20:47
-	12	((US-6465306-\$ or US-6445030-\$ or US-6436768-\$ or US-6418040-\$ or US-6327187-\$ or US-6005809-\$ or US-4353083-\$ or US-4635229-\$ or US-5739569-\$ or US-6448137-\$).did. or (US-20020151123-\$ or US-20020032891-\$ or US-20020060929-\$).did.) and (eras\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/15 20:47
-	332	(nonvolatile (non adj volatile) flash) and sonos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 19:43
-	164	((nonvolatile (non adj volatile) flash) and sonos) and (program\$4 writ\$3) and (eras\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 19:45
-	169	((nonvolatile (non adj volatile) flash) and sonos) and (eras\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 20:24
-	36	((nonvolatile (non adj volatile) flash) and sonos) and (eras\$3 near3 method)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 20:24
-	2943	(nonvolatile non-volatile flash) and (eras\$3 near3 method)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:32
-	374	((nonvolatile non-volatile flash) and (eras\$3 near3 method)) and (drain same gate same (ground near3 source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:25
-	0	(nonvolatile non-volatile flash) and ((eras\$3 near3 method) same (drain same gate same (ground near3 source)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:33

-	34	(nonvolatile non-volatile flash) and ((eras\$3 near3 method) same drain same gate same (ground near3 source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/12 16:33
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